



Product data sheet

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Features

- -30V,-4.0A, RDS(ON) =51mΩ@VGS = 10V
- Fast switching
- Green Device Available
- Suit for -2.5V Gate Drive Applications

Applications

- Notebook
- Load Switch
- Battery Protection
- Hand-Held Instruments

BVDSS	RDSON	ID
-30V	$51 \mathrm{m}\Omega$	-4.0A

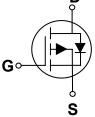
Absolute Maximum Ratings Tc=25°C unless otherwise noted

Symbol	Parameter	Rating	Units
Vds	Drain-Source Voltage	-30	V
Vgs	Gate-Source Voltage	±12	V
	Drain Current – Continuous (T _A =25°C)	-4.0	A
D	Drain Current – Continuous (T _A =70°C)	-3.0	A
Ідм	Drain Current – Pulsed ¹	- 15.4	Α
D-	Power Dissipation (T _A =25°C)	1.56	W
Po	Power Dissipation – Derate above 25°C	0.012	W/°C
Тѕтс	Storage Temperature Range	-55 to 150	°C
Tj	Operating Junction Temperature Range	-55 to 150	°C

Thermal Characteristics

Symbol	Parameter	Тур.	Max.	Unit
Reja	Thermal Resistance Junction to ambient		80	°C/W







Off Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	Vgs=0V , Id=-250uA	-30			V
BV_dss/T_J	BVDss Temperature Coefficient	Reference to 25℃ , I⊳=-1mA		-0.03		V/°C
	Drain Courses Lookage Current	Vds=-30V , Vgs=0V , Tj=25°C			- 1	uA
IDSS	Drain-Source Leakage Current	V⊳s=-24V , V₀s=0V , Tյ=125℃			- 10	uA
lgss	Gate-Source Leakage Current	Vgs= ±12V , Vds=0V			±100	nA

On Characteristics

		Vgs=-10V , Id=-4A		51	65	mΩ
RDS(ON)	Static Drain-Source On-Resistance	V _{GS} =-4.5V , I _D =-3A		65	80	mΩ
		Vgs=-2.5V , Id=-2A		85	100	mΩ
VGS(th)	Gate Threshold Voltage		-0.4	-0.9	-1.3	V
riangle VGS(th)	VGS(th) Temperature Coefficient	Vgs=Vds , Id =-250uA		3		mV/°C
gfs	Forward Transconductance	Vds=-10V , Id=-3A		5.4		S

Dynamic and switching Characteristics

Qg	Total Gate Charge ^{2,3}		 8	
Qgs	Gate-Source Charge ^{2,3}	Vds=-15V , Vgs=-4.5V , Id=-4A	 1.9	 nC
Qgd	Gate-Drain Charge ^{2,3}		 1.4	
Td(on)	Turn-On Delay Time ^{2,3}		 5.4	
Tr	Rise Time ^{2,3}	VDD=-15V , VGs=-10V ,	 19.4	
Td(off)	Turn-Off Delay Time ^{2,3}	Rg=6Ω Ip=-1A	 45.9	 ns
Tf	Fall Time ^{2,3}		 12.4	
Ciss	Input Capacitance		 810	
Coss	Output Capacitance	V _{DS} =-15V , V _{GS} =0V , F=1MHz	 85	 pF
Crss	Reverse Transfer Capacitance		 50	

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
ls	Continuous Source Current				-4.0	А
Іѕм	Pulsed Source Current	V _G =V _D =0V , Force Current			-8.0	А
Vsd	Diode Forward Voltage	Vgs=0V , Is=-1A , TJ=25°C			- 1.S	V

Note :

Repetitive Rating : Pulsed width limited by maximum junction temperature.
The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%.
Essentially independent of operating temperature.





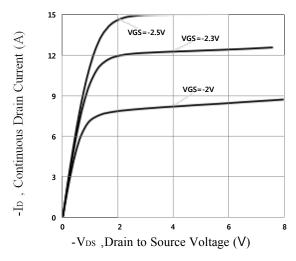
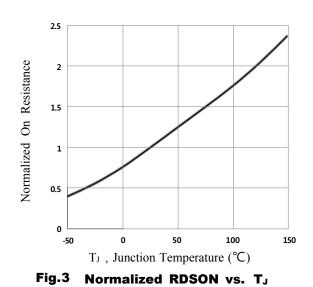
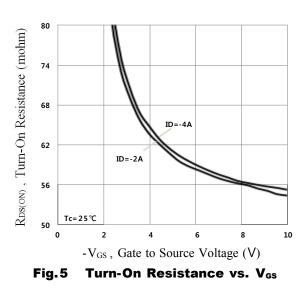


Fig.1 Typical Output Characteristics





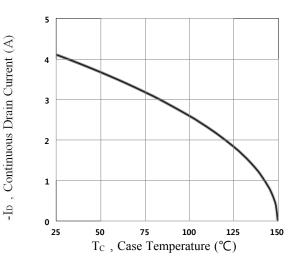
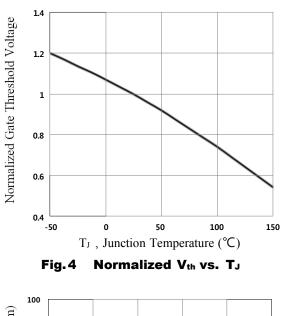
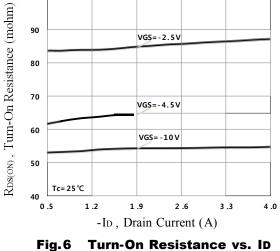


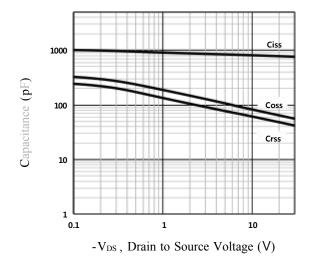
Fig.2 Continuous Drain Current vs. Tc













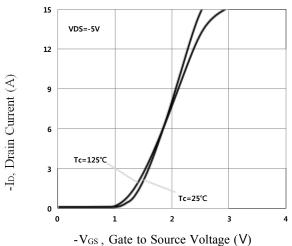


Fig.9 Transfer Characteristics

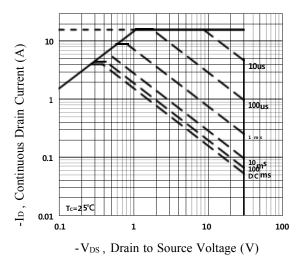


Fig.11 Maximum Safe Operation Area

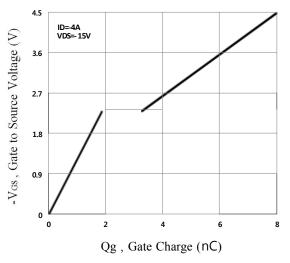


Fig.8 Gate Charge Characteristics

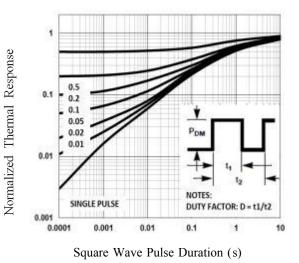
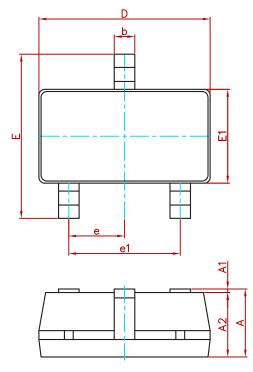


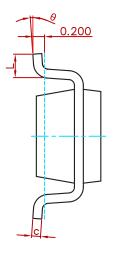
Fig. 10 Normalized Transient Impedance





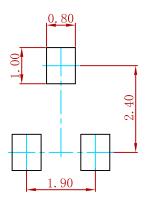
PACKAGE MECHANICAL DATA





Symbol	Dimensions In Millimeters		Dimension	s In Inches
Symbol	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
С	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
E	2.650	2.950	0.104	0.116
е	0.950(BSC)	0.037	(BSC)
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

Suggested Pad Layout



Note:

1.Controlling dimension:in millimeters.

2.General tolerance:± 0.05mm.3.The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
AO3401A	SOT-23-3L	3000





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